# MSKSEMI 美森科













FSD

TVS

TSS

MOV

GDT

PIFD

1N4148WT-MS

**Product specification** 





#### **Features**

- Fast switching speed
- Ultra-small surface mount package
- For general purpose switching applications
- High conductance

## **Reference News**

PACKAGE OUTLINE	Anode	Marking
		T4
SOD-523		

#### **RNNING**

PIN	DESCRIPTION	
1	Cathode	
2	Anode	

# **Absolute Maximum Ratings** (Ta = 25℃)

Parameter	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	$V_{RM}$	100	V
Reverse Voltage	V <sub>R</sub>	75	V
Average Rectified Forward Current	I <sub>F(AV)</sub>	125	mA
Forward Continuous Current	$I_{FM}$	250	mA
Non-repetitive Peak Forward Surge Current at $t = 1 \mu s$ at $t = 100 ms$	I <sub>FSM</sub>	2 1	А
Power Dissipation	P <sub>tot</sub>	150	mW
Thermal Resistance Junction to Ambient Air	$R_{\rm \grave{e}JA}$	833	°C/W
Operating Temperature Range	Tj	- 65 to + 150	${\mathbb C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 150	${\mathbb C}$

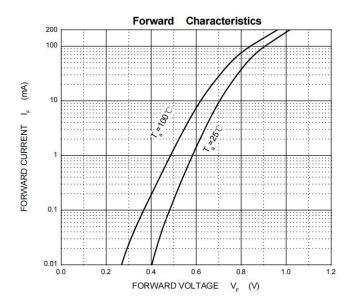


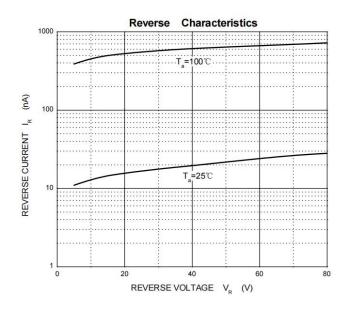
## Characteristics at Ta = 25 ℃

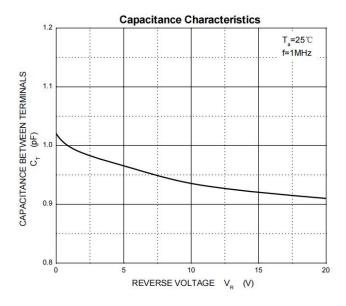
Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage	.,	75		V
at $I_R = 1 \mu A$	$V_{(BR)R}$	73	-	V
Forward Voltage				
at I <sub>F</sub> = 1 mA		_	0.715	
at I <sub>F</sub> = 10 mA	VF	-	0.855	V
at I⊧ = 50 mA		-	1	
at I <sub>F</sub> = 150 mA		-	1.25	
Peak Reverse Current				
at $V_R = 75 \text{ V}$		-	1	μA
at V <sub>R</sub> = 20 V	$I_{R}$	-	25	nA
at V <sub>R</sub> = 75 V, T <sub>J</sub> = 150 ℃		-	50	μA
at V <sub>R</sub> = 25 V, T <sub>J</sub> = 150 ℃		-	30	μA
Total Capacitance	C-		2	F
at $V_R = 0 V$ , $f = 1 MHz$	Ст	-	2	r r
Reverse Recovery Time	+		4	ns
at $I_{rr}$ = 0. 1 X $I_R$ , $I_F$ = $I_R$ = 10 mA, $R_L$ = 100 $\Omega$	t <sub>rr</sub>	-	4	110

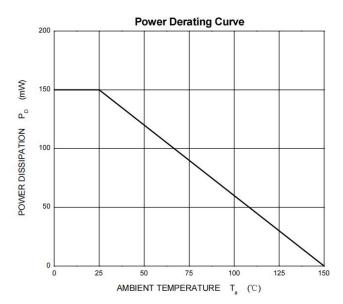


# **Typical Characteristics**



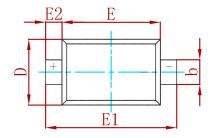


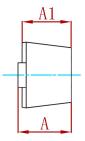


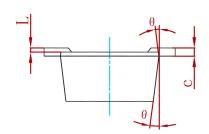




## PACKAGE MECHANICAL DATA

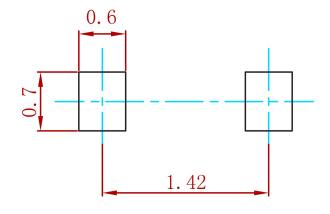






Cumbal	Dimensions In Millimeters		Dimensions In Inches	
Symbol	Min	Max	Min	Max
Α	0.510	0.770	0.020	0.031
A1	0.500	0.700	0.020	0.028
b	0.250	0.350	0.010	0.014
С	0.080	0.150	0.003	0.006
D	0.750	0.850	0.030	0.033
E	1.100	1.300	0.043	0.051
E1	1.500	1.700	0.059	0.067
E2	0.200	) REF	0.008	3 REF
L	0.010	0.070	0.001	0.003
9	7° F	REF	7° F	REF

# **Suggested Pad Layout**



#### Note:

- 1.Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

### **REEL SPECIFICATION**

P/N	PKG	QTY
1N4148WT-MS	SOD-523	3000



## **Attention**

- Any and all MSKSEMI Semiconductor products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your MSKSEMI Semiconductor representative nearest you before using any MSKSEMI Semiconductor products described or contained herein in such applications.
- MSKSEMI Semiconductor assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all MSKSEMI Semiconductor products described or contained herein.
- Specifications of any and all MSKSEMI Semiconductor products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer'sproducts or equipment.
- MSKSEMI Semiconductor. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with someprobability. It is possiblethat these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents—or events cannot occur. Such measures include but are not limited to protective circuits anderror prevention circuitsfor safedesign, redundant design, and structural design.
- In the event that any or all MSKSEMI Semiconductor products (including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from theauthorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of MSKSEMI Semiconductor.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. MSKSEMI Semiconductor believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. Whendesigning equipment, referto the "Delivery Specification" for the MSKSEMI Semiconductor productthat you intend to use.